

an active matrix circuit including a first plurality of thin film transistors formed on the insulating surface of the first substrate;

a driving circuit including a second plurality of thin film transistors formed over the insulating surface of the first substrate for driving said active matrix circuit;

a second substrate facing said first substrate with a liquid crystal material interposed therebetween, said first substrate having an extended portion which extends beyond at least one side edge of the second substrate;

at least one semiconductor integrated circuit chip disposed over the extended portion of the first substrate and operationally connected to said driving circuit,

wherein each of said first plurality of thin film transistors is a bottom gate type transistor in which a gate electrode is located below a channel region of the transistor, and each of said second plurality of thin film transistors is a top gate type transistor in which a gate electrode is located over a channel region of the transistor.

37. A device according to claim 36 wherein the channel region of each of the first plurality of thin film transistors is amorphous while the channel region of each of the second plurality of thin film transistors is crystalline.

38. A liquid crystal display device comprising:

a first substrate having an insulating surface;

an active matrix circuit including a first plurality of thin film transistors formed on the insulating surface of the first substrate;

a driving circuit including a second plurality of thin film transistors formed over the insulating surface of the first substrate for driving said active matrix circuit;

a second substrate facing said first substrate with a liquid crystal material interposed therebetween, said first substrate having an extended portion which extends beyond at least one side edge of the second substrate;